DS34LV86T 3V Enhanced CMOS

Quad Differential Line Receiver

DS34LV86T 3V Enhanced CMOS Quad Differential Line Receiver

General Description

The DS34LV86T is a high speed guad differential CMOS receiver that meets the requirements of both TIA/EIA-422-B and ITU-T V.11. The CMOS DS34LV86T features typical low static I_{CC} of 9 mA which makes it ideal for battery powered and power conscious applications. The TRI-STATE® enables, EN, allow the device to be disabled when not in use to minimize power consumption. The dual enable scheme allows for flexibility in turning receivers on and off.

The receiver output (RO) is guaranteed to be High when the inputs are left open. The receiver can detect signals as low as ±200 mV over the common mode range of ±10V. The receiver outputs (RO) are compatible with TTL and LVCMOS levels.

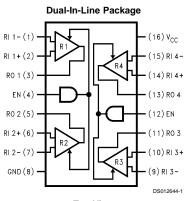
Features

- Low power CMOS design (30 mW typical)
- Interoperable with existing 5V RS-422 networks
- Industrial temperature range
- Meets TIA/EIA-422-B (RS-422) and ITU-T V.11 recommendation
- 3.3V Operation
- ±7V common mode range V_{ID} = 3V
- ±10V common mode range V_{ID} = 0.2V
- Receiver OPEN input failsafe feature
- Guaranteed AC parameter:

Maximum Receiver Skew: 4 ns Transition time: 10 ns

- Pin compatible with DS34C86T
- 32 MHz Toggle Frequency
- 6.5k ESD Tolerance (HBM)
- Available in SOIC packaging

Connection Diagram



Top View Order Number DS34LV86TN, DS34LV86TM See NS Package Number M16A or N16E

Truth Table

Enable EN	Inputs RI+-RI-	Output RO
L	Х	Z
Н	V _{ID} ≥ +0.2V	Н
Н	$V_{ID} \le -0.2V$	L
Н	Open†	Н

L = Logic Low

H = Logic High X = Irrelevant

Z = TRI-STATE

† = Open, Not Terminated

TRI-STATE® is a registered trademark of National Semiconductor Corporation.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC}) +7V
Enable Input Voltage (EN) +7V
Receiver Input Voltage

 $\begin{array}{lll} (V_{CM} \colon RI+, \, RI-) & \pm 14V \\ \text{Receiver Output Voltage (RO)} & -0.5V \text{ to } V_{CC} + 0.5V \\ \text{Receiver Output Current (RO)} & \pm 25 \text{ mA} \end{array}$

Maximum Package Power Dissipation +25°C

M Package 1190 mW N Package 1645 mW

Derate M Package 9.8 mW/°C above +25°C

Derate N Package 13.9 mW/°C above +25°C Storage Temperature Range 65°C to +150°C Lead Temperature Range Soldering (4 Seconds) +260°C ESD Ratings (HBM, 1.5k, 100 pF)

Receiver Inputs and Enables $\geq 6.5 \text{ kV}$ Other Pins $\geq 2 \text{ kV}$

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (V _{CC})	3.0	3.3	3.6	V
Operating Free Air				
Temperature (T _A)	-40	+25	+85	°C

Electrical Characteristics (Notes 2, 3)

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified.

Symbol	Parameter	Conditions	Pin	Min	Тур	Max	Units
V _{TH}	Differential Input Threshold	$V_{OUT} = V_{OH} \text{ or } V_{OL}$ -7V < V_{CM} < +7V	RI+, RI–	-200	±17.5	+200	mV
V _{HY}	Hysteresis	V _{CM} = 1.5V			35		mV
V _{IH}	Minimum High Level Input Voltage		EN	2.0			V
V _{IL}	Minimum Low Level Input Voltage		→ EN			0.8	V
R _{IN}	Input Resistance	V _{IN} = -7V, +7V (Other Input = GND)		5.0	8.5		kΩ
I _{IN}	Input Current	V _{IN} = +10V	T	0	1.1	1.8	mA
	(Other Input = 0V, Power On or V _{CC} = 0V)	V _{IN} = +3V	RI+, RI–	0	0.27		mA
		V _{IN} = 0.5V	_ KI-		-0.02		mA
		$V_{IN} = -3V$		0	-0.43		mA
		V _{IN} = -10V		0	-1.26	-2.2	mA
I _{EN}		V _{IN} = 0V to V _{CC}	EN			±1	μΑ
V _{OH}	High Level Output Voltage	$I_{OH} = -6 \text{ mA}, V_{ID} = +1V$ $I_{OH} = -6 \text{ mA}, V_{ID} = OPEN$		2.4	3		V
V _{OH}	High Level Output Voltage	$I_{OH} = -100 \mu A, V_{ID} = +1V$ $I_{OH} = -100 \mu A, V_{ID} = OPEN$			V _{CC} - 0.1		V
V _{OL}	Low Level Output Voltage	I _{OL} = +6 mA, V _{ID} = -1V	RO		0.13	0.5	V
l _{oz}	Output TRI-STATE Leakage Current	$V_{IN} = V_{CC}$ or GND EN = V_{IL}				±50	μA
I _{sc}	Output Short Circuit Current	$V_{O} = 0V, V_{ID} \ge 200 \text{ mV} $ (Note 4)		-10	-35	-70	mA
I _{cc}	Power Supply Current	No Load, All RI+, RI- = Open, EN = V _{CC} or GND	V _{cc}		9	15	mA

www.national.com

Switching Characteristics (Notes 3, 9, 10)

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
t _{PHL}	Propagation Delay High to Low	C _L = 15 pF	6	17.5	35	ns
t _{PLH}	Propagation Delay Low to High	(Figures 1, 2)	6	17.8	35	ns
t _r	Rise Time (20% to 80%)			4.1	10	ns
t _f	Fall Time (80% to 20%)			3.3	10	ns
t _{PHZ}	Disable Time	C _L = 50 pF			40	ns
t _{PLZ}	Disable Time	(Figures 3, 4)			40	ns
t _{PZH}	Enable Time				40	ns
t _{PZL}	Enable Time				40	ns
t _{SK1}	Skew, t _{PHL} - t _{PLH} (Note 5)	C _L = 15 pF		0.3	4	ns
t _{SK2}	Skew, Pin to Pin (Note 6)			0.6	4	ns
t _{SK3}	Skew, Part to Part (Note 7)			7	17	ns
f _{MAX}	Maximum Operating Frequency	C _L = 15 pF	32			MHz
	(Note 8)					

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" specifies conditions of device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except V_{ID}.

Note 3: All typicals are given for: $V_{CC} = +3.3V$, $T_A = +25^{\circ}C$.

Note 4: Short one output at a time to ground. Do not exceed package power dissipation ratings.

Note 5: t_{SK1} is the $\left|t_{PHL}-t_{PLH}\right|$ of a channel.

Note 6: t_{SK2} is the maximum skew between any two channels within a device, on either edge.

Note 7: t_{SK3} is the difference in propagation delay times between any channels of any devices. This specification (maximum limit) applies to devices within V_{CC} ±0.1V of one another, and a Delta $T_A = \pm 5$ °C (between devices) within the operating temperature range. This parameter is guaranteed by design and characterization.

Note 8: All channels switching, output duty cycle criteria is 40%/60% measured at 50% Input = 1V to 2V, 50% Duty Cycle, t_f/t_f ≤ 5 ns. This parameter is guaranteed by design and characterization.

Parameter Measurement Information

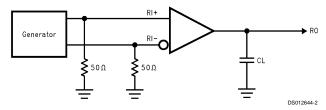


FIGURE 1. Receiver Propagation Delay and Transition Time Test Circuit (Notes 9, 10)

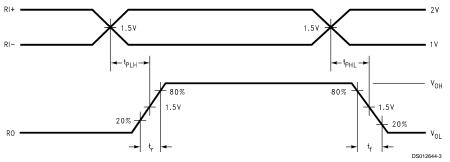


FIGURE 2. Receiver Propagation Delay and Transition Time Waveform (Notes 9, 10)

Note 9: Generator waveform for all tests unless otherwise specified: f = 1 MHz, Duty Cycle = 50%, $Z_O = 50\Omega$, $t_f \le 10$ ns. Note 10: C_L includes probe and jig capacitance.

Parameter Measurement Information (Continued)

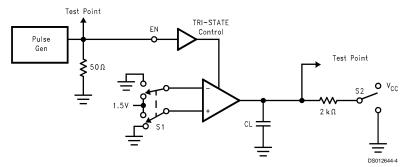


FIGURE 3. Receiver TRI-STATE Test Circuit

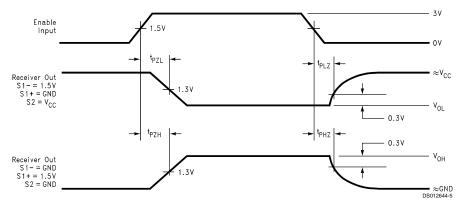


FIGURE 4. Receiver TRI-STATE Output Enable and Disable Waveforms (Notes 9, 10)

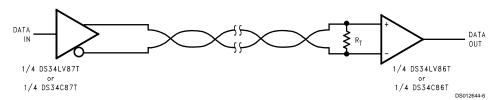
Typical Application Information

General application guidelines and hints for differential drivers receivers may be found in the following application notes:

AN-214, AN-457, AN-805, AN-847, AN-903, AN-912, AN-916

Power Decoupling Recommendations: Bypass caps must be used on power pins. High frequency ceramic (surface mount is recommended) 0.1 μF in parallel with 0.01 μF at the power supply pin. A 10 μF or greater solid tantalum or electrolytic should be connected at the power entry point on the printed circuit board.

Typical Application Information (Continued)



R_T is optional although highly recommended to reduce reflection

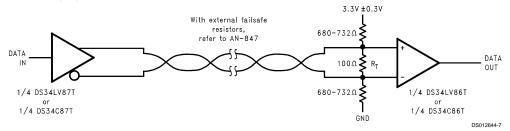


FIGURE 5. Typical Receiver Connections

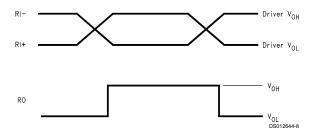


FIGURE 6. Typical Receiver Output Waveforms

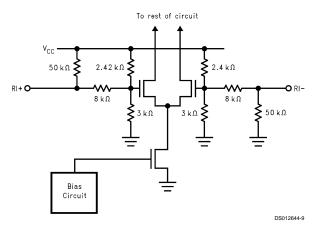
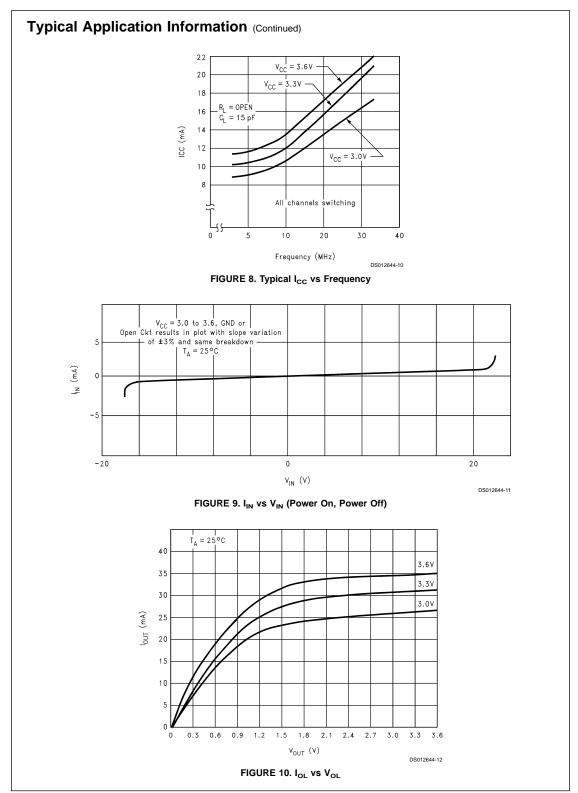


FIGURE 7. Typical Receiver Input Circuit





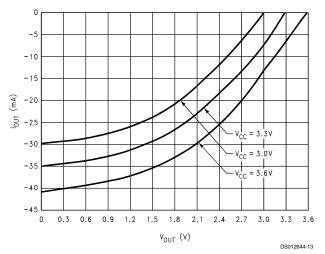
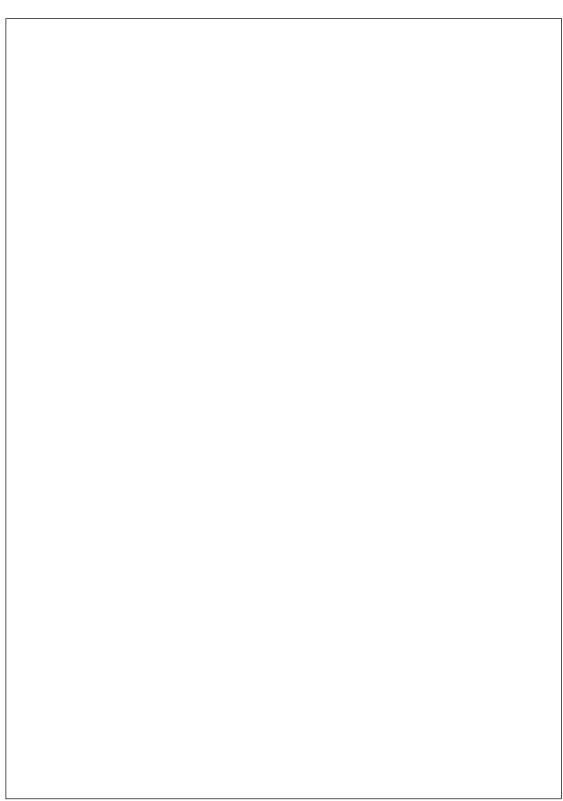
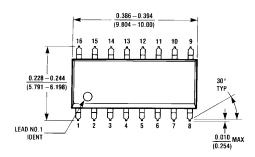
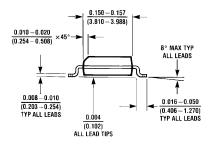


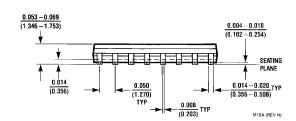
FIGURE 11. $I_{\rm OH}$ vs $V_{\rm OH}$



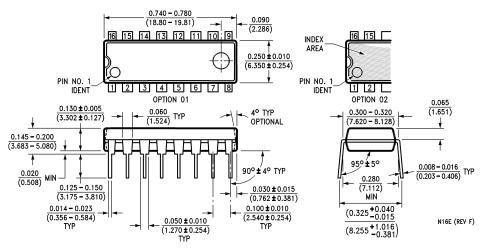








Dual-In-Line Package Order Number DS34LV86TM NS Package Number M16A



Dual-In-Line Package Order Number DS34LV86TN See NS Package Number N16E

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DE-VICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMI-CONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor Corporation Americas

Fax: 1-800-737-7018 Email: support@nsc.com

www.national.com

National Semiconductor Europe

Fax: +49 (0) 1 80-530 85 86 Fax: +49 (0) 1 80-530 85 86
Email: europe support@nsc.com
Deutsch Tel: +49 (0) 1 80-530 85 85
English Tel: +49 (0) 1 80-532 78 32
Français Tel: +49 (0) 1 80-532 93 58
Italiano Tel: +49 (0) 1 80-534 16 80

National Semiconductor Asia Pacific Customer Response Group Fax: 65-2504466 Email: sea.support@nsc.com National Semiconductor Japan Ltd. Tel: 81-3-5620-6175 Fax: 81-3-5620-6179